

■ ■ APPLICATION: Audio Frequency Low Power Amplifier Applications.

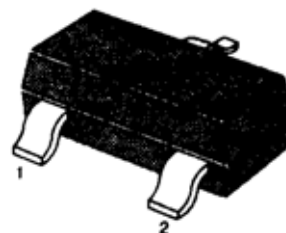
—PNP silicon—

Driver Stage Amplifier Applications.

■ ■ MAXIMUM RATINGS (Ta=25°C)

SOT-323

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-35	V
Collector-emitter voltage	V _{CEO}	-30	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-500	mA
Collector Power Dissipation	P _c	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



1. Base 2. Emitter 3. Collector

■ ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE1}	70		700		V _{CE} = -1V, I _c = -100mA
	h _{FE2}	25				V _{CE} = -6V, I _c = -400mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -35V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -5V, I _c =0
Collector-Base Breakdown Voltage	BV _{CBO}	-35			V	I _c = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-30			V	I _c = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.1	-0.25	V	I _c = -100mA, I _B = -10mA
Gain bandwidth product	f _r	100	200		MHz	I _c = -20mA, V _{CE} = -6V
Common Base Output Capacitance	C _{ob}		13		PF	V _{CB} = -6V, I _E =0, f = 1MHz

■ ■ h_{FE} Classification And Marking

Print Mark	ZO	ZY	ZG	ZL
Classification	O	Y	GR	BL
h _{FE1}	70~140	120~240	200~400	350~700